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## **Table of Content**

#### Session J1: Joint Plenary Session

J1-1 Logic Technology Scaling: Present and Future...1

#### Session J2: Joint Special Session - In-Memory Computing (All Invited)

- J2-1 Challenges of Computation-in-Memory Circuits for AI Edge Applications...2
- J2-2 Introduction of 3D AND-type Flash Memory and It's Applications to Computing-in-Memory (CIM)...4
- J2-3 Neurocomputing and Neurooptimization with Stochastic Memristive Networks...6

#### Session J3: Joint Plenary Session

J3-2 Finding a Needle in a Haystack: Success Stories of Data Mining and Machine Learning for Electronic Materials Selection...7

Session J4-1: Joint Special Session - Design-Technology Co-Optimization and Advanced Packaging (I) (All invited)

J4-1-1 Design/System Technology Co-Optimization for 3nm Node and Beyond...8

#### Session J4-2: Joint Special Session - Design-Technology Co-Optimization and Advanced Packaging (II) (All invited)

J4-2-1 From Design to System-Technology Optimization for CMOS ... 9

J4-2-2 Active Silicon Chiplet-Based Interposer for Exascale High Performance

Computing...11

#### Session J6: Joint Plenary Session

J6-2 Domain-specific In-memory Computing Architecture: CMOS Annealing Machine to Solve Combinatorial Optimization Problems...13

#### Session T1: Advanced CMOS Technology

- T1-1 FinFET Plus: A Scalable FinFET Architecture with 3D Air-Gap and Air-Spacer Toward the 3nm Generation and Beyond...15
- T1-2 The First Ge Nanosheets GAAFET CMOS Inverters Fabricated by 2D Ge/Si Multilayer Epitaxy, Ge/Si Selective Etching...17
- T1-3 Sub-60 mV/dec Germanium Nanowire Field-Effect Transistors with 2-nm-thick Ferroelectric Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub>...19
- T1-4 The Powerful Methods of Flicker Noise Improvement in 22nm Technology...21
- T1-5 Si Cryo-CMOS and Quantum Dots for Quantum Computing Applications...23

#### Session T2: Special Session-Heterogeneous Integration (All Invited)

- T2-1 3D Integration of Memories Including Heterogeneous Integration...25
- T2-2 Silicon Photonic Integrated Circuit Technology with Wafer Level Integrated Lasers...27
- T2-3 New Directions in Silicon Photonics: From Optical Communications to the Brain...28

#### Session T3: Poster Session

- T3-1 A 500V SOI-LIGBT With Multiple Deep-Oxide Trenches For Fast Turn-OFF...29
- T3-2 Back-Gate Network Extraction Free from Dynamic Self-Heating in FD SOI...31
- T3-3 Suppressed Source-to-Drain Tunneling and Short-Channel Effects for MFIS-type InGaAs and Si Negative-Capacitance FinFETs...33
- T3-4 Benchmarking the Performance of Heterogeneous Stacked RRAM with CFETSRAM and MRAM for Deep Neural Network Application Amidst Variation and Noise...35
- T3-5 Transfer Characteristics of CMOS Inverter Using "Steep SS PN-Body Tied SOI-FET"...37
- T3-6 Analysis of Drain Current Enhancement in "PN-Body Tied SOI-FET"Bulk vs Surface Conduction Mode and Low Vds Saturation Effect-...39
- T3-7 Calculation of Field Dependent Mobility in MoS2 and WS2 with Multi-Valley Monte Carlo Method...41
- T3-8 Improved Switching Time in Negative Capacitance Junctionless Transistors...43
- T3-9 Machine Learning Approach to Predicting Tunnel Field-Effect Transistors...45
- T3-10 A Precise Debugging Method and Defect Diagnosis with Mass Big-Data Analysis in the Designed High-Dense Array for Rapid Yield Improvement in a Logic Platform...47
- T3-11 A Novel Design of Ferroelectric Nanowire Tunnel Field Effect Transistors...49
- T3-12 Ferroelectric Characterization in Ultrathin Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> MFIS Capacitors by Piezoresponse Force Microscopy (PFM) in Vacuum...51
- T3-13 Selective Area Epitaxy of Axial Wurtzite -InAs Nanowire on InGaAs NW by MOCVD...53
- T3-14 Impact of Interfacial Layer on the Switching Characteristics of HZO-Based Ferroelectric Tunnel Junction...55
- T3-15 Alleviation of Charge Trapping and Flicker Noise in HfZrO<sub>2</sub>–Based Ferroelectric Capacitors by Thermal Engineering...57
- T3-16 Improvement of Nanotwinned Copper Thermal Stability for High Temperature Heterogeneous Integration...59
- T3-17 TCAD Validation of an Intercept-at-Zero-Gate-Length MOSFET Series Resistance Extraction Method...61

#### T3-18 Design of a Low Power Approximate Adder Based on Magnetic Tunnel Junction for Image Processing Applications...63

#### Session T4: Non-Volatile Memories

- T4-1 The Pursuit of Atomistic Switching and Cross Point Memory...65
- T4-2 An 8kb Spin-Orbit-Torque Magnetic Random-Access Memory...67
- T4-3 Ultrahigh Spin-Orbit Torque Efficiency at Spin Reorientation Transition State in Pt/Co Multilayer...69
- T4-4 Multi-Bit Cryogenic Flash Memory on Si/SiGe and Ge/GeSi Heterostructures...71
- T4-5 Bandgap-Engineered Tunneling Layer on Operation Characteristics of Poly-Ge Charge-Trapping Flash Memory Devices...73
- T4-6 A Twin Bit AND-Type Multiple-Time-Programming Memory Cell by Nano-scaled High  $\kappa$  Metal Gate Process...75

#### Session T5: Oxide Transistors and BEOL/Process Technology

- T5-1 BEOL Compatible Indium-Tin-Oxide Transistors: Switching of Ultra-High-Density 2D Electron Gas over 0.8×10<sup>14</sup> /cm<sup>2</sup> by Ferroelectric Polarization...77
- T5-2 Double-Layer Amorphous InGaZnO Thin Film Transistors with High Mobility and High Reliability...79
- T5-3 Grain Structure Resistivity Relationship of Ru ALD Precursors...81
- T5-4 Asymmetric Low Temperature Cu-Polymer Hybrid Bonding with Au Passivation Layer...83
- T5-5 On-Wafer Electronic Layer Detectors Array (ELDA) for e-beam Imaging in Advanced Lithographic Systems...85

#### Session T6: Special Session-Low Temperature Electronics (All Invited)

- T6-1 Cryo-CMOS Interfaces for Large-Scale Quantum Computers...87
- T6-2 Cryogenic Electronics and Materials for the Quantum Era...88
- T6-3 Cool-CMOS Technology for Next Generation High Performance Computing...89
- T6-4 Development of FD-SOI Cryogenic Amplifier for Application to STJ Readout in COBAND Project...90

#### Session T7: Power and RF Devices

- T7-1 High Voltage Gain 4H-SiC CMOS Technology Featuring LOCal Oxidation of SiC (LOCOSiC) Isolation and Balanced Gate Dielectric...92
- T7-2 CMOS-Compatible GaN HEMT on 200mm Si-substrate for RF application...94

- T7-3 Superior High-Frequency Performance of T-Gated Poly-Si TFTs...96
- T7-4 FD-SOI mm-Wave Differential Single-Pole Switches with Ultra-High Isolation...98

# Session T8: Special Session- Low Dimensional Materials and Devices (All Invited)

- T8-1 Carbon Nanotube Transistors for Future Technology Nodes...100
- T8-2 Uncovering the Deformations in Two-Dimensional Lateral Heterojunctions...101
- T8-3 2D Layered Semiconductor: Challenge & Perspective...102
- T8-4 Monolayer Optoelectronics and Their Excitonic Properties...104
- T8-5 Theoretical Study of Electronic Transport in Two-Dimensional Materials...105
- T8-6 Top-Gated Carbon Nanotube FETs from Quantum Simulations: Comparison with Experiments...107

#### Session T9: Special Session- Hardware Security (All Invited)

- T9-1 Quantum Tunneling PUF: a Chip Fingerprint for Hardware Security...109
- T9-2 Proof of Authenticity of Logistics Information with Passive RFID Tags and Blockchain...111
- T9-3 Overview of Memory Security Technologies...113
- T9-4 Hardware Security Back to the Future...115

#### Session T10: Ferroelectric FETs and Memories

- T10-1 Ferroelectric and Antiferroelectric Hf/Zr Oxide Films: Past, Present and Future (Invited)...116
- T10-2 Current Percolation Path Impacting Switching Behavior of Ferroelectric FETs...118
- T10-3 DFT Models of Ferroelectric Hafnium-Zirconium Oxide Stacks With and Without Dielectric Interlayers...120
- T10-4 Ultra-thin Hf<sub>0.5</sub>Zr<sub>0.5</sub>O<sub>2</sub> Ferroelectric Tunnel Junction with High Current Density...122
- T10-5 Three-dimensional (3D) Non-volatile SRAM with IWO Transistor and HZO Ferroelectric Capacitor...124
- T10-6 Comparison of 2-T FeFET Nonvolatile Memory Cells: Gate Select vs. Drain Select...126

#### Session T11: Biomedical Sensors and Devices (All Invited)

- T11-1 Internet of Medical Things for Diagnosing Musculoskeletal Injuries...128
- T11-2 Autopilot, Smart IoT Devices for Accelerating the Development of Bio-Electronic Medicine...129
- T11-3 New Horizons for Silicon Nanotechnology in Healthcare...130

T11-4 How can Chip Technology Realize Electronic Sensing of Viruses?...131

Organization

**Author Index**